

# OKI Semiconductor

## MSM51V16400A

4,194,304-Word × 4-Bit DYNAMIC RAM : FAST PAGE MODE TYPE

### DESCRIPTION

The MSM51V16400A is a 4,194,304-word × 4-bit dynamic RAM fabricated in OKI's CMOS silicon gate technology. The MSM51V16400A achieves high integration, high-speed operation, and low-power consumption due to quadruple polysilicon double metal CMOS. The MSM51V16400A is available in a 26/24-pin plastic SOJ or 26/24-pin plastic TSOP.

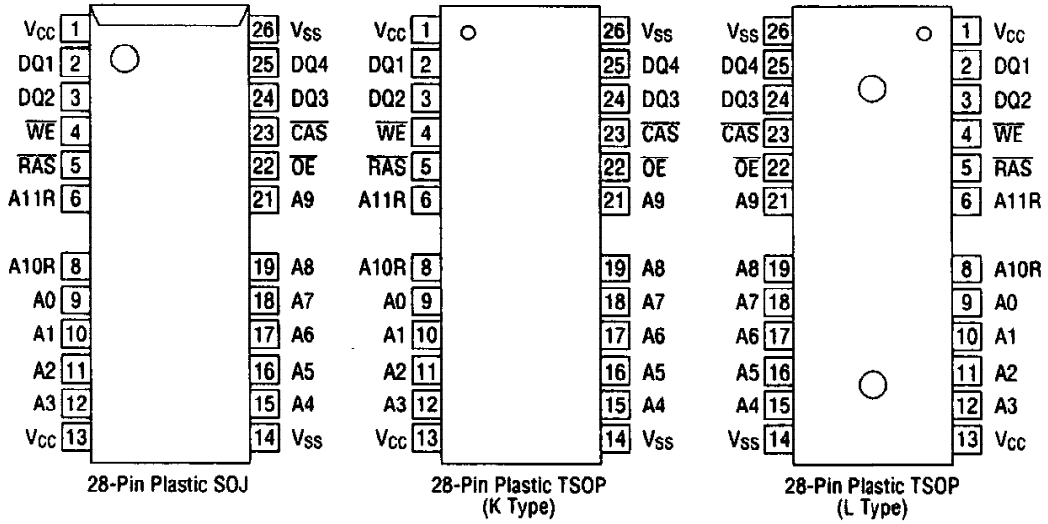
### FEATURES

- 4,194,304-word × 4-bit configuration
- Single 3.3 V power supply, ±0.3 V tolerance
- Input : LVTTTL compatible, low input capacitance
- Output : LVTTTL compatible, 3-state
- Refresh : 4096 cycles/64 ms
- Fast page mode, read modify write capability
- $\overline{\text{CAS}}$  before  $\overline{\text{RAS}}$  refresh, hidden refresh,  $\overline{\text{RAS}}$ -only refresh capability
- Multi-bit test mode capability
- Package options:
  - 26/24-Pin 300 mil plastic SOJ (SOJ26/24-P-300) (Product : MSM51V16400A-xxSJ)
  - 26/24-Pin 300 mil plastic TSOP (TSOP26/24-P-300-K) (Product : MSM51V16400A-xxTS-K)
  - (TSOP26/24-P-300-L) (Product : MSM51V16400A-xxTS-L)xx indicates speed rank.

### PRODUCT FAMILY

Family	Access Time (Max.)				Cycle Time (Min.)	Power Dissipation	
	t <sub>RAC</sub>	t <sub>AA</sub>	t <sub>CAC</sub>	t <sub>OE</sub>		Operating (Max.)	Standby (Max.)
MSM51V16400A-60	60 ns	30 ns	15 ns	15 ns	110 ns	360 mW	3.6 mW
MSM51V16400A-70	70 ns	35 ns	20 ns	20 ns	130 ns	324 mW	
MSM51V16400A-80	80 ns	40 ns	20 ns	20 ns	150 ns	288 mW	

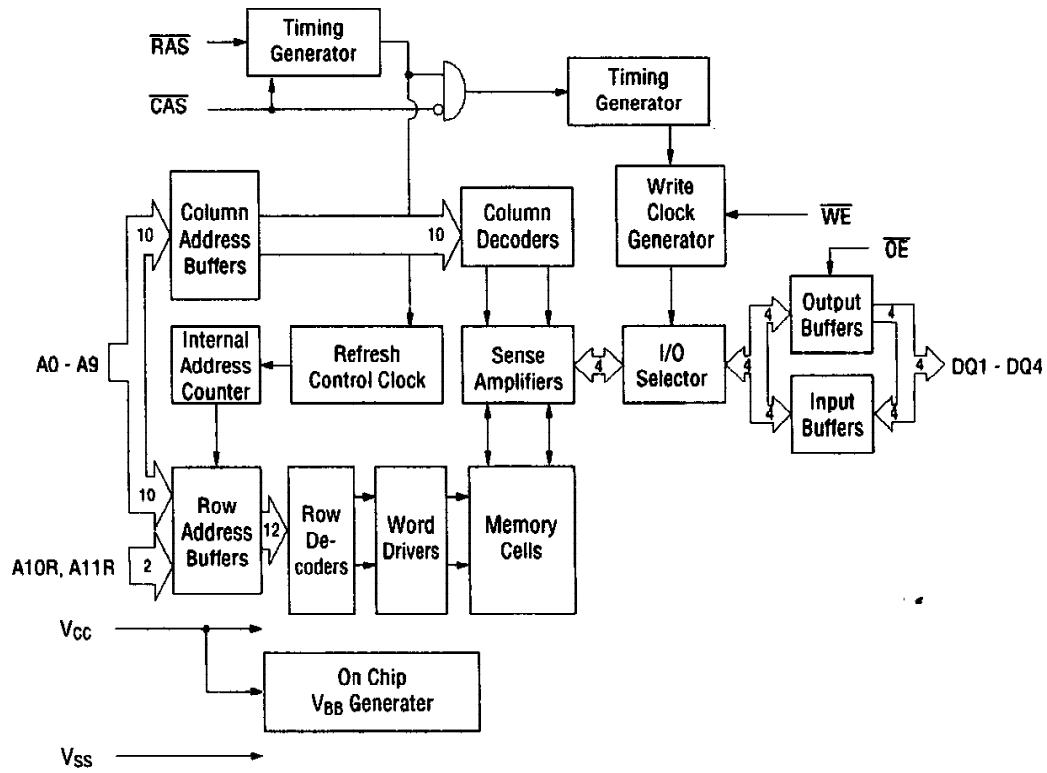
**PIN CONFIGURATION (TOP VIEW)**



Pin Name	Function
A0 - A9, A9R - A11R	Address Input
RAS	Row Address Strobe
CAS	Column Address Strobe
DQ1 - DQ4	Data Input/Data Output
OE	Output Enable
WE	Write Enable
V <sub>CC</sub>	Power Supply (3.3 V)
V <sub>SS</sub>	Ground (0 V)

Note : The same power supply voltage must be provided to every V<sub>CC</sub> pin, and the same GND voltage level must be provided to every V<sub>SS</sub> pin.

**BLOCK DIAGRAM**



**ELECTRICAL CHARACTERISTICS****Absolute Maximum Ratings**

Parameter	Symbol	Rating	Unit
Voltage on Any Pin Relative to V <sub>SS</sub>	V <sub>T</sub>	-0.5 to 4.6	V
Short Circuit Output Current	I <sub>OS</sub>	50	mA
Power Dissipation	P <sub>D</sub> *	1	W
Operating Temperature	T <sub>opr</sub>	0 to 70	°C
Storage Temperature	T <sub>stg</sub>	-55 to 150	°C

\*: Ta = 25°C

**Recommended Operating Conditions**

(Ta = 0°C to 70°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Power Supply Voltage	V <sub>CC</sub>	3.0	3.3	3.6	V
	V <sub>SS</sub>	0	0	0	V
Input High Voltage	V <sub>IH</sub>	2.0	—	V <sub>CC</sub> + 0.3	V
Input Low Voltage	V <sub>IL</sub>	-0.3	—	0.8	V

**Capacitance**(V<sub>CC</sub> = 3.3 V ±0.3 V, Ta = 25°C, f = 1 MHz)

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance (A0 - A9, A10R, A11R)	C <sub>IN1</sub>	—	6	pF
Input Capacitance (RAS, CAS, WE, OE)	C <sub>IN2</sub>	—	7	pF
Output Capacitance (DQ1 - DQ4)	C <sub>I/O</sub>	—	10	pF

DC Characteristics

(V<sub>CC</sub> = 3.3 V ± 0.3 V, T<sub>a</sub> = 0°C to 70°C)

Parameter	Symbol	Condition	MSM51V16400 A-60		MSM51V16400 A-70		MSM51V16400 A-80		Unit	Note
			Min.	Max.	Min.	Max.	Min.	Max.		
			Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = -2.0 mA	2.4	V <sub>CC</sub>	2.4		
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 2.0 mA	0	0.4	0	0.4	0	0.4	V	
Input Leakage Current	I <sub>LI</sub>	0 V ≤ V <sub>I</sub> ≤ V <sub>CC</sub> + 0.3 V, All other pins not under test = 0 V	-10	10	-10	10	-10	10	μA	
Output Leakage Current	I <sub>LO</sub>	DQ disable 0 V ≤ V <sub>O</sub> ≤ 3.6 V	-10	10	-10	10	-10	10	μA	
Average Power Supply Current (Operating)	I <sub>CC1</sub>	$\overline{RAS}$ , $\overline{CAS}$ cycling, t <sub>RC</sub> = Min.	—	100	—	90	—	80	mA	1, 2
Power Supply Current (Standby)	I <sub>CC2</sub>	$\overline{RAS}$ , $\overline{CAS} = V_{IH}$	—	2	—	2	—	2	mA	1
		$\overline{RAS}$ , $\overline{CAS}$ ≥ V <sub>CC</sub> - 0.2 V	—	0.5	—	0.5	—	0.5		
Average Power Supply Current (RAS-only Refresh)	I <sub>CC3</sub>	$\overline{RAS}$ cycling, $\overline{CAS} = V_{IH}$ , t <sub>RC</sub> = Min.	—	100	—	90	—	80	mA	1, 2
Power Supply Current (Standby)	I <sub>CC5</sub>	$\overline{RAS} = V_{IH}$ , $\overline{CAS} = V_{IL}$ , DQ = enable	—	5	—	5	—	5	mA	1
Average Power Supply Current (CAS before RAS Refresh)	I <sub>CC6</sub>	$\overline{RAS}$ cycling, $\overline{CAS}$ before $\overline{RAS}$	—	100	—	90	—	80	mA	1, 2
Average Power Supply Current (Fast Page Mode)	I <sub>CC7</sub>	$\overline{RAS} = V_{IL}$ , $\overline{CAS}$ cycling, t <sub>PC</sub> = Min.	—	90	—	80	—	70	mA	1, 3

- Notes :
1. I<sub>CC</sub> Max. is specified as I<sub>CC</sub> for output open condition.
  2. Address can be changed once or less while  $\overline{RAS} = V_{IL}$ .
  3. Address can be changed once or less while  $\overline{CAS} = V_{IH}$ .

## AC Characteristics (1/2)

(V<sub>CC</sub> = 3.3 V ±0.3 V, T<sub>a</sub> = 0°C to 70°C) Note 1, 2, 3, 11, 12

Parameter	Symbol	MSM51V16400 A-60		MSM51V16400 A-70		MSM51V16400 A-80		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.		
		Random Read or Write Cycle Time	t <sub>RC</sub>	110	—	130	—		
Read Modify Write Cycle Time	t <sub>RWC</sub>	155	—	185	—	205	—	ns	
Fast Page Mode Cycle Time	t <sub>PC</sub>	40	—	45	—	50	—	ns	
Fast Page Mode Read Modify Write Cycle Time	t <sub>PRWC</sub>	85	—	100	—	105	—	ns	
Access Time from $\overline{\text{RAS}}$	t <sub>RAC</sub>	—	60	—	70	—	80	ns	4, 5, 6
Access Time from $\overline{\text{CAS}}$	t <sub>CAC</sub>	—	15	—	20	—	20	ns	4, 5
Access Time from Column Address	t <sub>AA</sub>	—	30	—	35	—	40	ns	4, 6
Access Time from $\overline{\text{CAS}}$ Precharge	t <sub>CPA</sub>	—	35	—	40	—	45	ns	4
Access Time from $\overline{\text{OE}}$	t <sub>OEA</sub>	—	15	—	20	—	20	ns	4
Output Low Impedance Time from $\overline{\text{CAS}}$	t <sub>CLZ</sub>	0	—	0	—	0	—	ns	4
CAS to Data Output Buffer Turn-off Delay Time	t <sub>OFF</sub>	0	15	0	20	0	20	ns	7
$\overline{\text{OE}}$ to Data Output Buffer Turn-off Delay Time	t <sub>OEZ</sub>	0	15	0	20	0	20	ns	7
Transition Time	t <sub>T</sub>	3	50	3	50	3	50	ns	3
Refresh Period	t <sub>REF</sub>	—	64	—	64	—	64	ms	
RAS Precharge Time	t <sub>RP</sub>	40	—	50	—	60	—	ns	
RAS Pulse Width	t <sub>RAS</sub>	60	10,000	70	10,000	80	10,000	ns	
RAS Pulse Width (Fast Page Mode)	t <sub>RASP</sub>	60	100,000	70	100,000	80	100,000	ns	
RAS Hold Time	t <sub>RSH</sub>	15	—	20	—	20	—	ns	
RAS Hold Time referenced to $\overline{\text{OE}}$	t <sub>ROH</sub>	10	—	10	—	10	—	ns	
$\overline{\text{CAS}}$ Precharge Time (Fast Page Mode)	t <sub>CP</sub>	10	—	10	—	10	—	ns	
$\overline{\text{CAS}}$ Pulse Width	t <sub>CAS</sub>	15	10,000	20	10,000	20	10,000	ns	
$\overline{\text{CAS}}$ Hold Time	t <sub>CSH</sub>	60	—	70	—	80	—	ns	
CAS to $\overline{\text{RAS}}$ Precharge Time	t <sub>CRP</sub>	10	—	10	—	10	—	ns	
CAS to $\overline{\text{RAS}}$ Precharge Time	t <sub>RHCP</sub>	35	—	40	—	45	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	t <sub>RCD</sub>	20	45	20	50	20	60	ns	5
$\overline{\text{RAS}}$ to Column Address Delay Time	t <sub>RAD</sub>	15	30	15	35	15	40	ns	6
Row Address Set-up Time	t <sub>ASR</sub>	0	—	0	—	0	—	ns	
Row Address Hold Time	t <sub>RAH</sub>	10	—	10	—	10	—	ns	
Column Address Set-up Time	t <sub>ASC</sub>	0	—	0	—	0	—	ns	
Column Address Hold Time	t <sub>CAH</sub>	15	—	15	—	15	—	ns	
Column Address Hold Time from $\overline{\text{RAS}}$	t <sub>AR</sub>	50	—	55	—	60	—	ns	
Column Address to $\overline{\text{RAS}}$ Lead Time	t <sub>RAL</sub>	30	—	35	—	40	—	ns	
Read Command Set-up Time	t <sub>RCS</sub>	0	—	0	—	0	—	ns	
Read Command Hold Time	t <sub>RCH</sub>	0	—	0	—	0	—	ns	8
Read Command Hold Time referenced to $\overline{\text{RAS}}$	t <sub>RRH</sub>	0	—	0	—	0	—	ns	8

AC Characteristics (2/2)

(V<sub>CC</sub> = 3.3 V ±0.3 V, T<sub>a</sub> = 0°C to 70°C) Note 1, 2, 3, 11, 12

Parameter	Symbol	MSM51V16400 A-60		MSM51V16400 A-70		MSM51V16400 A-80		Unit	Note
		Min.	Max.	Min.	Max.	Min.	Max.		
		Write Command Set-up Time	t <sub>WCS</sub>	0	—	0	—		
Write Command Hold Time	t <sub>WCH</sub>	10	—	15	—	15	—	ns	
Write Command Hold Time from RAS	t <sub>WCR</sub>	45	—	55	—	60	—	ns	
Write Command Pulse Width	t <sub>WP</sub>	10	—	10	—	10	—	ns	
OE Command Hold Time	t <sub>OEH</sub>	15	—	20	—	20	—	ns	
Write Command to RAS Lead Time	t <sub>RWL</sub>	15	—	20	—	20	—	ns	
Write Command to CAS Lead Time	t <sub>CWL</sub>	15	—	20	—	20	—	ns	
Data-in Set-up Time	t <sub>DS</sub>	0	—	0	—	0	—	ns	10
Data-in Hold Time	t <sub>DH</sub>	15	—	15	—	15	—	ns	10
Data-in Hold Time from RAS	t <sub>DHR</sub>	50	—	55	—	60	—	ns	
OE to Data-in Delay Time	t <sub>OED</sub>	15	—	20	—	20	—	ns	
CAS to WE Delay Time	t <sub>CWD</sub>	40	—	50	—	50	—	ns	9
Column Address to WE Delay Time	t <sub>AWD</sub>	55	—	65	—	70	—	ns	9
RAS to WE Delay Time	t <sub>RWD</sub>	85	—	100	—	110	—	ns	9
CAS Precharge WE Delay Time	t <sub>CPWD</sub>	60	—	70	—	75	—	ns	9
CAS Active Delay Time from RAS Precharge	t <sub>RPC</sub>	10	—	10	—	10	—	ns	
RAS to CAS Set-up Time (CAS before RAS)	t <sub>CSR</sub>	10	—	10	—	10	—	ns	
RAS to CAS Hold Time (CAS before RAS)	t <sub>CHR</sub>	20	—	20	—	20	—	ns	
CAS Precharge Time (Refresh Counter Test)	t <sub>CPT</sub>	40	—	40	—	40	—	ns	
WE to RAS Precharge Time (CAS before RAS)	t <sub>WRP</sub>	10	—	10	—	10	—	ns	
WE Hold Time from RAS (CAS before RAS)	t <sub>WRH</sub>	10	—	10	—	10	—	ns	
RAS to WE Set-up Time (Test Mode)	t <sub>WTS</sub>	10	—	10	—	10	—	ns	
RAS to WE Hold Time (Test Mode)	t <sub>WTH</sub>	20	—	20	—	20	—	ns	

- Notes:
1. A start-up delay of 200  $\mu$ s is required after power-up, followed by a minimum of eight initialization cycles ( $\overline{\text{RAS}}$ -only refresh or  $\overline{\text{CAS}}$  before  $\overline{\text{RAS}}$  refresh) before proper device operation is achieved.
  2. The AC characteristics assume  $t_T = 5$  ns.
  3.  $V_{IH}$  (Min.) and  $V_{IL}$  (Max.) are reference levels for measuring input timing signals. Transition times ( $t_T$ ) are measured between  $V_{IH}$  and  $V_{IL}$ .
  4. This parameter is measured with a load circuit equivalent to 1 TTL load and 100 pF. Output timing reference levels are  $V_{OH} = 2.0$  V and  $V_{OL} = 0.8$  V.
  5. Operation within the  $t_{RCD}$  (Max.) limit ensures that  $t_{RAC}$  (Max.) can be met.  $t_{RCD}$  (Max.) is specified as a reference point only. If  $t_{RCD}$  is greater than the specified  $t_{RCD}$  (Max.) limit, access time is controlled by  $t_{CAC}$ .
  6. Operation within the  $t_{RAD}$  (Max.) limit ensures that  $t_{RAC}$  (Max.) can be met.  $t_{RAD}$  (Max.) is specified as a reference point only. If  $t_{RAD}$  is greater than the specified  $t_{RAD}$  (Max.) limit, access time is controlled by  $t_{AA}$ .
  7.  $t_{OFF}$  (Max.) and  $t_{OEZ}$  (Max.) define the time at which the output achieves the open circuit condition and are not referenced to output voltage levels.
  8.  $t_{RCH}$  or  $t_{RRH}$  must be satisfied for a read cycle.
  9.  $t_{WCS}$ ,  $t_{CWD}$ ,  $t_{RWD}$ ,  $t_{AWD}$  and  $t_{CPWD}$  are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If  $t_{WCS} \geq t_{WCS}$  (Min.), the cycle is an early write cycle and the data out will remain open circuit (high impedance) throughout the entire cycle. If  $t_{CWD} \geq t_{CWD}$  (Min.),  $t_{RWD} \geq t_{RWD}$  (Min.),  $t_{AWD} \geq t_{AWD}$  (Min.) and  $t_{CPWD} \geq t_{CPWD}$  (Min.), the cycle is a read modify write cycle and data out will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
  10. These parameters are referenced to  $\overline{\text{CAS}}$  leading edge in an early write cycle, and to  $\overline{\text{WE}}$  leading edge in an  $\overline{\text{OE}}$  control write cycle or a read modify write cycle.
  11. The test mode is initiated by performing a  $\overline{\text{WE}}$  and  $\overline{\text{CAS}}$  before  $\overline{\text{RAS}}$  refresh cycle. This mode is latched and remains in effect until the exit cycle is generated. In a test mode CA0 and CA1 are not used and each DQ pin now accesses 4-bit locations. Since all 4 DQ pins are used, a total of 16 data bits can be written in parallel into the memory array. In a read cycle, if 4 data bits are equal, the DQ pin will indicate a high level. If the 4 data bits are not equal, the DQ pin will indicate a low level. The test mode is cleared and the memory device returned to its normal operating state by performing a  $\overline{\text{RAS}}$ -only refresh cycle or a  $\overline{\text{CAS}}$  before  $\overline{\text{RAS}}$  refresh cycle.
  12. In a test mode read cycle, the value of access time parameters is delayed for 5 ns for the specified value. These parameters should be specified in test mode cycle by adding the above value to the specified value in this data sheet.

### See ADDENDUM G for AC Timing Waveforms